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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538-6470 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **ANNAPRAGADA, Rao, V.** [IN/US]; 34268 Pinnacles Drive, Union City, CA 94587 (US). **MOREY, Ian, J.** [AU/SG]; 15 Libra Drive, 576457 Singapore (SG). **HO, Chok, W.** [US/US]; 372 Meadowhaven Way, Milpitas, CA 95035 (US).

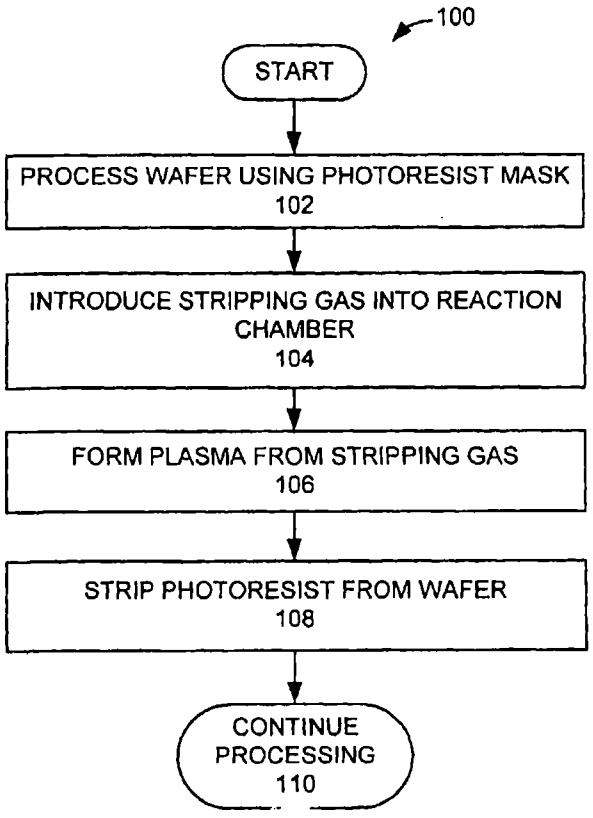
(74) Agent: **OLYNICK, Mary, R.**; Beyer Weaver & Thomas, LLP., P.O. Box 778, Berkeley, CA 94704-0778 (US).

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(54) Title: PHOTORESIST STRIP WITH 02 AND NH3 FOR ORGANOSILICATE GLASS APPLICATIONS



(57) Abstract: Process for stripping photoresist from a semiconductor wafer formed with at least one layer of OSG dielectric. The stripping process may be formed in situ or ex situ with respect to other integrated circuit fabrication processes. The process includes a reaction may be oxidative or reductive in nature. The oxidative reaction utilizes an oxygen plasma. The reductive reaction utilizes an ammonia plasma. The process of the present invention results in faster ash rates with less damage to the OSG dielectric than previously known stripping methods.

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ACTION

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